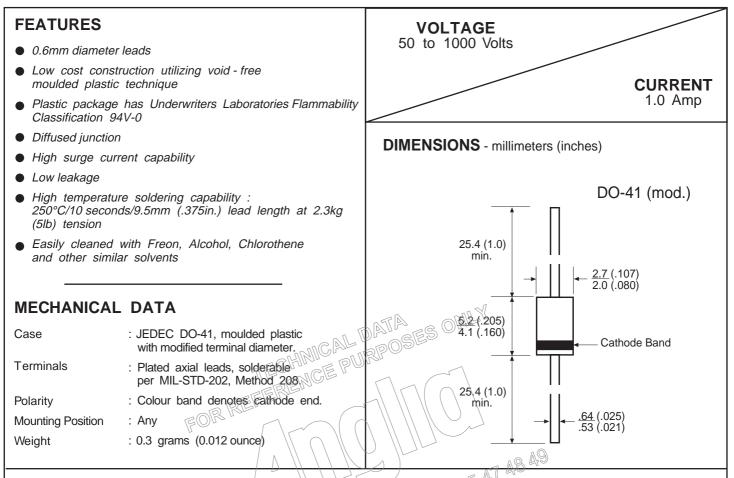


1 AMP SILICON RECTIFIERS 1N4001S THRU 1N4007S

TECHNICAL SPECIFICATION



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load, For capacitive load, derate current by 20%.

-		1	1N4001S	1N4002S	1N4003S	1N4004S	1N4005S	1N4006S	1N4007S	Units
Maximum Recurrent Peak Reverse Voltage		V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage		V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current 9.5mm (.375in.) Lead Length at $T_A = 75^{\circ}C$		I _{F(AV)}	1.0							А
Peak Forward Surge Current, 8.3 ms single half sine - wave superimposed on rated load		I _{FSM}	30							А
Maximum Instantaneous Forward Voltage at 1.0A		V _F	1.1							V
Maximum Reverse Current at Rated DC Blocking Voltage	TA= 25°C	- I _R	5.0							μA
	TA= 100°C		50							μA
Maximum Full load Reverse Current Full Cycle Average, 9.5mm (.375in.) Lead Length at $T_L = 75^{\circ}C$		I _{R(AV)}	30							μA
Typical Junction Capacitance (see Note 1)		CJ	30							pF
Typical Thermal Resistance (see Note 2)		R _{THja}	50							°C/W
Operating Temperature Range		TJ	- 50 to + 175							
Storage Temperature Range		T _{STG}	- 50 to + 175							°C

Notes :

1. Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts

2. Thermal Resistance from Junction to Ambient



1N4001S THRU 1N4007S

RATING AND CHARACTERISTIC CURVES

